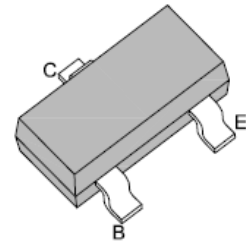


SMD General Purpose Transistor (PNP)

Features

- PNP Silicon Epitaxial Planar Transistor for Switching and Amplifier Applications
- RoHS compliance



Mechanical Data

SOT-23



Case:	SOT-23, Plastic Package
Terminals:	Solderable per MIL-STD-202G, Method 208
Weight:	0.008 gram

Maximum Ratings *(T_{Ambient}=25°C unless noted otherwise)*

Symbol	Description	MMBT2907A	Unit	Conditions
	Marking Code	2F		
-V_{CEO}	Collector-Emitter Voltage (Open Base)	60	V	
-V_{CBO}	Collector-Base Voltage (Open Emitter)	60	V	
-V_{EBO}	Emitter-Base Voltage (Open Collector)	5.0	V	
-I_C	Collector Current (D.C)	600	mA	
P_{tot}	Power Dissipation above 25°C	250	mW	
f_T	Transition Frequency at f= 100MHz	200	MHz	-I _C =50mA, -V _{CE} =20V
R_{θj-a}	From junction to ambient in free air	500	K/W	
T_J	Junction Temperature	150	°C	
T_{STG}	Storage Temperature Range	-55 to +150	°C	

SMD General Purpose Transistor (PNP)

MMBT2907A

Electrical Characteristics ($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

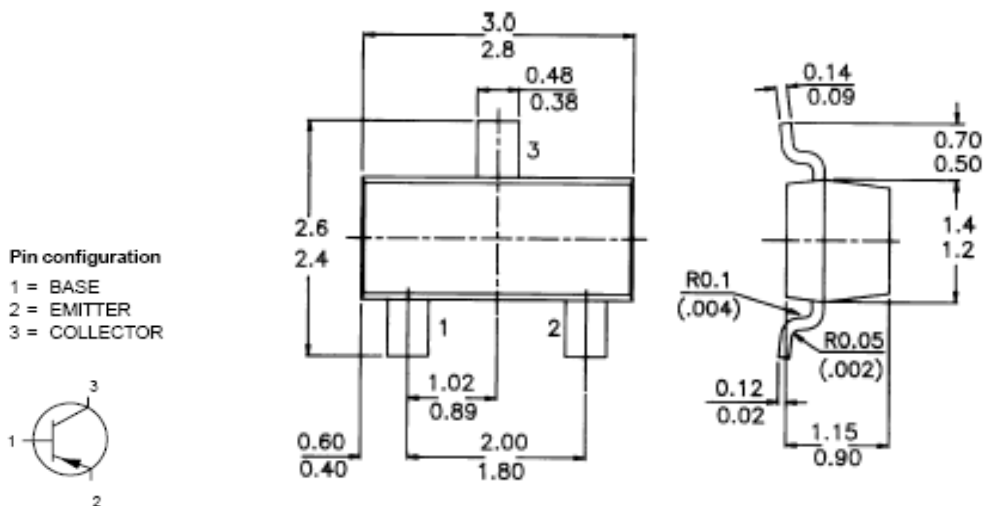
Symbol	Description	Min.	Max.	Unit	Conditions
hFE	D.C. Current Gain	75	-		$-V_{CE}=10V, -I_C=0.1mA$
		100	-		$-V_{CE}=10V, -I_C=1mA$
		100	-		$-V_{CE}=10V, -I_C=10mA$
		100	300		$-V_{CE}=10V, -I_C=150mA$
		50	-		$-V_{CE}=10V, -I_C=500mA$
-ICBO	Collector Cut-Off Current	-	10	nA	$-V_{CB}=50V, I_E=0$
		-	10	μA	$-V_{CB}=50V, I_E=0, T_j=125^{\circ}C$
-ICEX		-	50	nA	$-V_{EB}=0.5V, -V_{CE}=30V$
-IBEX	Base Current with Reverse Biased Emitter Junction	-	50	nA	$-V_{EB}=3V, -V_{CE}=30V$
-VCEsat	Collector-Emitter Saturation Voltage	-	0.4	V	$-I_C=150mA, -I_B=15mA$
		-	1.6		$-I_C=500mA, -I_B=50mA$
-VBEsat	Base-Emitter Saturation Voltage	-	1.3	V	$-I_C=150mA, -I_B=15mA$
		-	2.6		$-I_C=500mA, -I_B=50mA$
-V(BR)CEO	Collector-Emitter Breakdown Voltage	60	-	V	$-I_C=10mA, I_B=0$
-V(BR)CBO	Collector-Base Breakdown Voltage	60	-	V	$-I_C=10\mu A, I_E=0$
-V(BR)EBO	Emitter-Base Breakdown Voltage	5.0	-	V	$-I_E=10\mu A, I_C=0$
fT	Current Gain-Bandwidth Product	200	-	MHz	$-V_{CE}=20V, -I_C=50mA, f=100MHz$
Co	Output Capacitance	-	8.0	pF	$-V_{CB}=10V, f=1.0MHz, I_E=0$
Ci	Input Capacitance	-	30	pF	$-V_{EB}=2.0V, f=1.0MHz, I_C=0$
ton	Turn on Time	-	45	ns	$-I_B=15mA$ $-I_C=150mA$ $-V_{CC}=30V$
td	Delay Time	-	10		
tr	Rise Time	-	40		
toff	Turn-Off Time (ts + tf)	-	100	ns	$-I_B=15mA$ $-I_C=150mA$ $-V_{CC}=6V$
ts	Storage Time	-	80		
tf	Fall Time	-	30		

SMD General Purpose Transistor (PNP)

MMBT2907A

Dimensions in mm

SOT-23



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